

# DSILC6-4xx

## ESD Protection for high speed interface

## **Main applications**

Where transient over-voltage protection in ESD sensitive equipment is required, such as:

- Computers
- Printers
- Communication systems
- Cell phone handsets and accessories
- Video equipment

## Description

The **DSILC6-4xx** is a monolithic application specific discrete dedicated to ESD protection of high speed interfaces, such as USB 2.0, Ethernet, **display and camera serial interfaces** (LVDS).

The device is ideal for applications where both reduced printed circuit board space and power absorption capability are required.

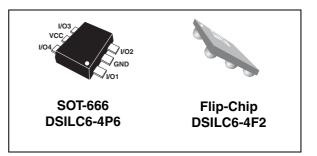
### Features

Diode array topology

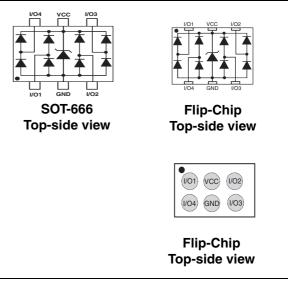
- 4 line protection
- 5 V V<sub>CC</sub> protection
- Very low capacitance: 1 pF typ.
- Lead-free pacakge
- RoHS compliant

### **Benefits**

- Very low capacitance between lines to GND for optimized data integrity
- Low PCB space consumption: 2.9 mm<sup>2</sup> max for SOT-666 and 1.5 mm<sup>2</sup> max for Flip-Chip
- Cut-off frequency > 2 GHz
- High reliability offered by monolithic integration
- MDDI, SMIA, MIPI specification compliant



### **Functional diagram**



### **Order Code**

Part Number	Marking
DSILC6-4P6	G
DSILC6-4F2	EI

### Complies with the following standards:

IEC 61000-4-2 level 4:

8 kV (contact discharge)

15 kV (air discharge)

MIL STD 883G-Method 3015-7: class 3B

May 2007

www.st.com

## 1 Characteristics

### Table 1.Absolute ratings

Symbol	Parameter			Value	Unit	
V <sub>PP</sub>	Peak pulse voltage	IEC 61000-4-2 contact discharge IEC 61000-4-2 air discharge		8 15	kV	
	I <sub>PP</sub> Peak pulse current		SOT-666	5	٨	
IPP		I/O to GND Pulse waveform = 8/20 μs	Flip-Chip	7	A	
Р			SOT-666	90	W	
P <sub>PP</sub>	Peak pulse power		Flip-Chip	120	vv	
T <sub>stg</sub>	Storage temperature range			-55 to +150	°C	
Tj	Maximum junction temperature			125	°C	
ΤĹ	Lead solder temperature (10 seconds duration)			260	°C	

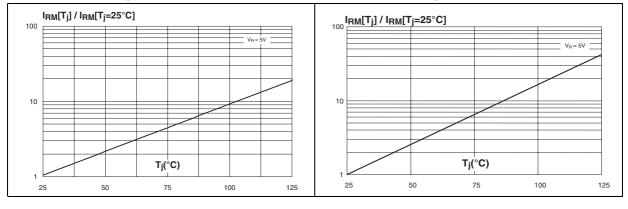
### Table 2.Electrical characteristics ( $T_{amb} = 25^{\circ} C$ )

Symbol	Parameter	
V <sub>RM</sub>	Reverse stand-off voltage	
I <sub>RM</sub>	Leakage current	VBR VF
$V_{BR}$	Breakdown voltage	
V <sub>F</sub>	Forward voltage	
V <sub>CL</sub>	Clamping voltage	Slope = 1/Rd
I <sub>PP</sub>	Peak pulse current	<b>↓</b>

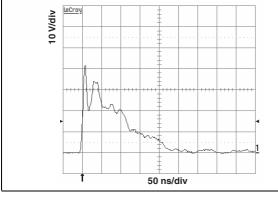
Symbol Parameter		Test Conditions		Value			Unit
				Min	Тур	Max	Unit
I <sub>RM</sub>	Leakage current	V <sub>RM</sub> = 5 V				0.5	μA
V <sub>BR</sub>	Breakdown voltage between V <sub>BUS</sub> and GND	I <sub>R</sub> = 1 mA		6			V
V <sub>F</sub>	Forward voltage	I <sub>F</sub> = 10 mA				1	V
		$V_{I/O} = 0 \text{ V}, \text{ F} = 1 \text{ MHz}, \text{ V}_{OSC} = 30 \text{ mV}$	SOT-666		2	2.5	
Capacitance between	Capacitance between		Flip-Chip		2.5	3	
℃i/o-GND	Ci/o-GND I/O and GND	$V_{I/O} = 1.65 \text{ V}, V_{CC} = 4.3 \text{ V},$	SOT-666		1.5	1.8	
	F = 1 MHz, V <sub>OSC</sub> = 400 mV	Flip-Chip		1.8	2.0		
			SOT-666		1.0	1.25	~F
C <sub>i/o-i/o</sub> Capacitance between I/O	V <sub>I/O</sub> = 0 V, F = 1 MHz, V <sub>OSC</sub> = 30 mV	Flip-Chip		1.25	1.5	pF	
	V <sub>I/O</sub> = 1.65 V, V <sub>CC</sub> = 4.3 V,	SOT-666		0.75	0.9		
	F = 1 MHz, V <sub>OSC</sub> = 400 mV Flip-Chip			0.9	1.20		
$\Delta C_{i/o-GND}$		V <sub>I/O</sub> = 0 V, F = 1 MHz, V <sub>OSC</sub> = 30 mV				0.06	
ΔC <sub>i/o-i/o</sub>		V <sub>I/O</sub> = 0 V, F = 1 MHz, V <sub>OSC</sub> = 30 mV				0.05	

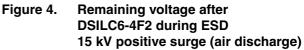
#### Figure 1. Relative variation of leakage current versus junction temperature - SOT-666 (typical values)

#### Figure 2. Relative variation of leakage current versus junction temperature Flip-Chip (typical values)



#### Figure 3. Remaining voltage after DSILC6-4P6 during ESD 15 kV positive surge (air discharge)





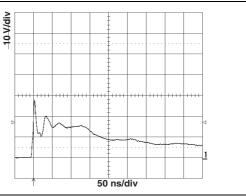
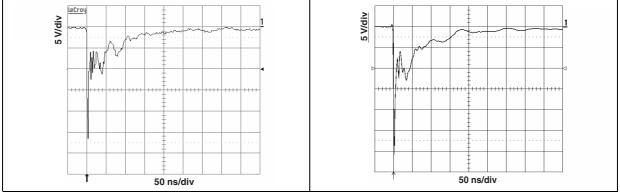


 Figure 5.
 Remaining voltage after
 Figure 6.
 Remaining voltage after

 DSILC6-4P6 during ESD
 DSILC6-4F2 during ESD
 DSILC6-4F2 during ESD

 15 kV negative surge (air discharge)
 15 kV negative surge (air discharge)



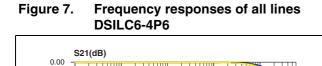
· /

- 5.00

- 10.00

- 15.00

-20.00



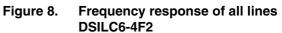
F(Hz)

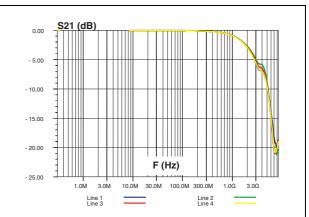
100.0M

Line 2 Line 4 1.0G

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10.0M





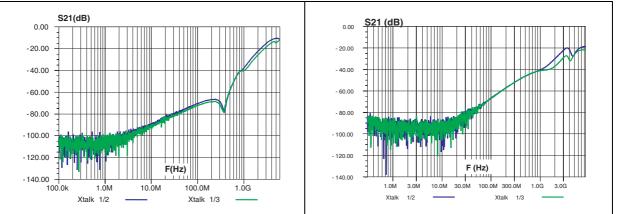


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1.0M

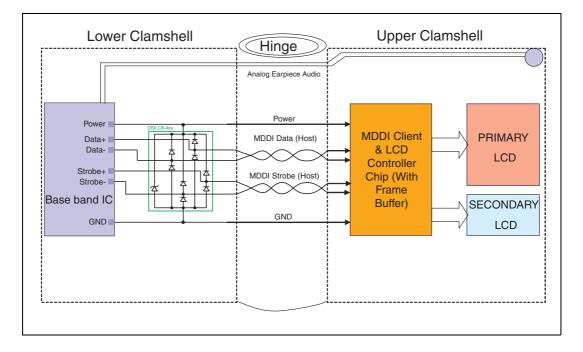
Line 1 Line 3

Figure 10. Crosstalk results for lines 1/2 and 1/3 DSILC6-4F2

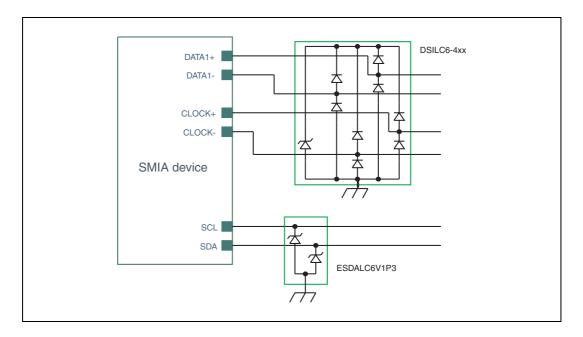


## 2 Application examples

### 2.1 MDDI



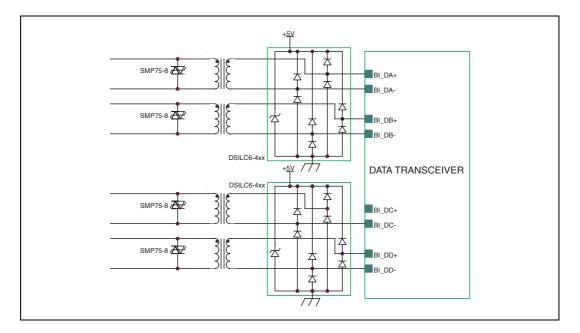
## 2.2 SMIA



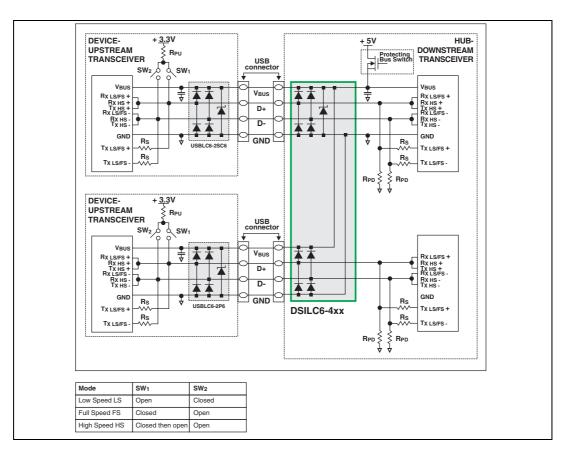


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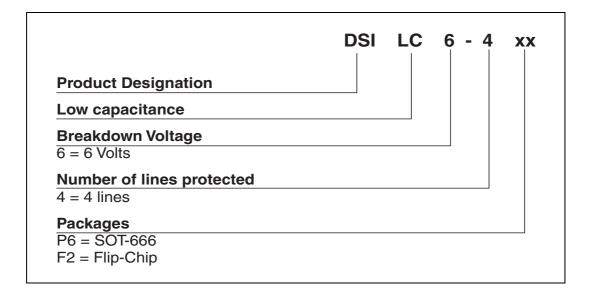
### 2.3 Ethernet 1 Gb



## 2.4 USB 2.0



## **3** Ordering information scheme



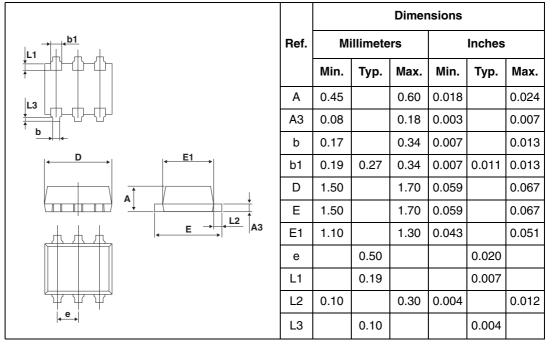


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## 4 Package information

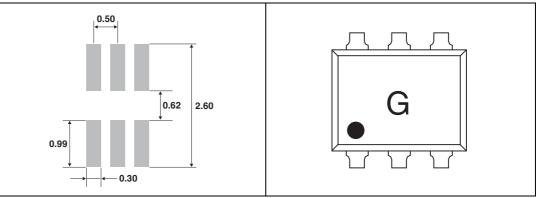
• Epoxy meets UL94, V0

#### Table 3.SOT-666 Dimensions

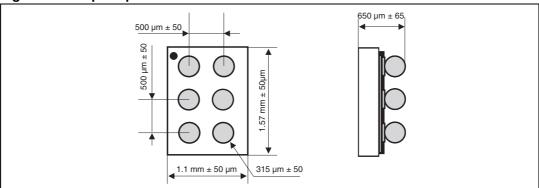


#### Figure 11. SOT-666 footprint

#### Figure 12. SOT-666 marking







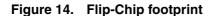
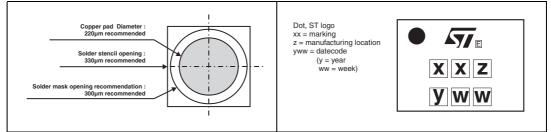
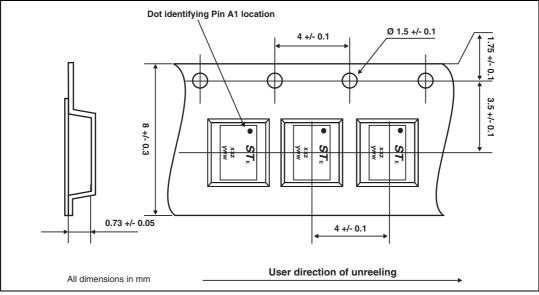


Figure 15. Flip-Chip marking







In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.



## 5 Ordering information

Ordering code	Ordering code Marking		Package Weight Base qty		Delivery mode
DSILC6-4P6	G	SOT-666	2.9 mg	3000	Tape and reel
DSILC6-4F2	El	Flip-Chip	2.22 mg	5000	Tape and reel

## 6 Revision history

Date	Revision	Description of Changes	
10-Aug-2006	1	Initial release.	
04-Jan-2007	2	Added Flip-Chip package. Added applications examples for SMIA, Ethernet 1 Gb, and USB. Updated Tj max to 150. Added $V_{\rm RM}$ line in Table 2. Modified MDDI example figure.	
28-May-2007	3	Modified Functional diagram on page 1 to show Top side view instead of Bump side view of DSILC64F2. Removed $V_{RM}$ line in Table 2. Added characteristic curves specific to each package fo ESD, Frequency response and Crosstalk	

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